Photo Semiconductor Device - Page 1 of 1



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Inclosure Material:	
Metal and plastic	
Overall Length:	
Between 0.180 inches and 0.210 inches	
Terminal Length:	
0.500 inches	
Overall Diameter:	
Between 0.209 inches and 0.230 inches	
Function For Which Designed:	
Phototransistor	
Internal Configuration:	
Junction contact	
Electrode Internally-electrically Connected To Case:	
Collector	
Mounting Method:	
Terminal	
Terminal Circle Diameter:	
0.100 inches	
Features Provided:	
Hermetically sealed case	
Semiconductor Material:	
Silicon	
Voltage Rating In Volts Per Characteristic:	
80.0 collector to base voltage/static/emitter open and 50.0 collector to emitter voltage/static/base open and 7.0 emitter to co	ollector voltage,
dc	
Power Rating Per Characteristic:	
250.0 milliwatts small-signal input power, common-collector absolute	
Maximum Operating Tempurature Per Measurement Point:	
200.0 degrees celsius junction	
Special Features:	
Junction pattern arrangement: npn	
Terminal Type And Quantity:	
3 uninsulated wire lead	
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
No	
Fiig:	
A110a0	